



Axial lead diode

Schottky barrier rectifiers diodes

SB 3020 ... SB 3040

Forward Current: 30 A

Reverse Voltage: 20 to 100 V

Features

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0

Mechanical Data

- Plastic case: $\text{AE } 8 \times 7,8$ [mm]
- Weight approx.: 2,4 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 500 pieces per Ammo

- 1) Valid, if leads are kept at ambient temperature at a distance of 6 mm from case
- 2) $I_F = 5 \text{ A}$, $T_J = 25 \text{ }^\circ\text{C}$
- 3) $T_A = 25 \text{ }^\circ\text{C}$
- 4) Thermal resistance from junction to lead/terminal at a distance 0 mm from case
- 5) Max. junction temperature $T_J \leq 150 \text{ }^\circ\text{C}$ ($V_R \leq 80 \% V_{RRM}$) in reverse mode and $T_J \leq 200 \text{ }^\circ\text{C}$ in bypass mode

Type	Repetitive peak reverse voltage V_{RRM} V	Surge peak reverse voltage V_{RSM} V	Max. reverse recovery time $I_F = -A$ $I_R = -A$ $I_{RR} = -A$ t_{rr} ns	Max. forward voltage $V_F^{(2)}$
SB 3020	20	20	-	0,39
SB 3030	30	30	-	0,39
SB 3040	40	40	-	0,39

Absolute Maximum Ratings		$T_A = 25 \text{ }^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
I_{FAV}	Max. averaged fwd. current, R-load, $T_A = 70 \text{ }^\circ\text{C}^{(1)}$	30	A
I_{FRM}	Repetitive peak forward current $f > 15 \text{ Hz}^{(1)}$	90	A
I_{FSM}	Peak forward surge current 50 Hz half sinus-wave $^{(3)}$	650	A
i^2t	Rating for fusing, $t < 10 \text{ ms}^{(3)}$	2100	A^2s
R_{thA}	Max. thermal resistance junction to ambient $^{(1)}$		K/W
R_{thL}	Max. thermal resistance junction to terminals $^{(4)}$	1	K/W
T_j	Operating junction temperature	- 50 ... + 150 ($T_J \leq 200 \text{ }^\circ\text{C}$ in bypass mode $^{(5)}$)	$^\circ\text{C}$
T_s	Storage temperature	- 50 ... + 175	$^\circ\text{C}$

Characteristics		$T_A = 25 \text{ }^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
I_R	Maximum leakage current, $T_j = 25 \text{ }^\circ\text{C}$; $V_R = V_{RRM}$	<600	μA
	$T_j = 125 \text{ }^\circ\text{C}$; $V_R = V_{RRM}$	<70	mA
C_j	Typical junction capacitance (at MHz and applied reverse voltage of V)	-	pF
Q_{rr}	Reverse recovery charge ($U_R = V$; $I_F = A$; $dI_F/dt = \text{A/ms}$)	-	μC
E_{RSM}	Non repetitive peak reverse avalanche energy ($I_R = \text{mA}$; $T_j = \text{ }^\circ\text{C}$; inductive load switched off)	-	mJ



